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APPLICATION NO.	I	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.	
10/716,785		11/19/2003	Wu-Song Huang	FIS920030377US1	6138	
32074	7590	07/18/2006		EXAMINER		
	_	BUSINESS MAC	LEE, SIN J			
DEPT. 18G BLDG. 300-				ART UNIT	PAPER NUMBER	
2070 ROUT	E 52		1752			
HOPEWEL	L JUNCT	ION, NY 12533	DATE MAILED: 07/18/2006			

Please find below and/or attached an Office communication concerning this application or proceeding.

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		Application No.	Applicant(s)	—— <u>l</u>
Office Action Summary		10/716,785	HUANG ET AL.	
		Examiner	Art Unit	
		Sin J. Lee	1752	
Period fo	The MAILING DATE of this communication app or Reply	pears on the cover sheet with the c	orrespondence addres	S
WHIC - Exte after - If NC - Failu Any	ORTENED STATUTORY PERIOD FOR REPLY CHEVER IS LONGER, FROM THE MAILING DANSIONS of time may be available under the provisions of 37 CFR 1.13 SIX (6) MONTHS from the mailing date of this communication. O period for reply is specified above, the maximum statutory period were to reply within the set or extended period for reply will, by statute, reply received by the Office later than three months after the mailing ed patent term adjustment. See 37 CFR 1.704(b).	ATE OF THIS COMMUNICATION 36(a). In no event, however, may a reply be tir will apply and will expire SIX (6) MONTHS from , cause the application to become ABANDONE	N. nely filed the mailing date of this commur (D) (35 U.S.C. § 133).	
Status				
1)⊠	Responsive to communication(s) filed on 28 Ap	<u>pril 2006</u> .		
2a)⊠	This action is FINAL . 2b) ☐ This	action is non-final.		
3)[Since this application is in condition for allowar	·		rits is
	closed in accordance with the practice under E	Ex parte Quayle, 1935 C.D. 11, 4	53 O.G. 213.	
Disposit	ion of Claims			
5)□ 6)⊠ 7)⊠	Claim(s) <u>1,2,5,7-16,19 and 21-30</u> is/are pending 4a) Of the above claim(s) is/are withdraw Claim(s) is/are allowed. Claim(s) <u>1,2,5,7-16,19 and 21-30</u> is/are rejected Claim(s) <u>12,13,25 and 26</u> is/are objected to. Claim(s) are subject to restriction and/or	wn from consideration.		
Applicat	ion Papers			
10)	The specification is objected to by the Examine The drawing(s) filed on is/are: a) acceeds applicant may not request that any objection to the Replacement drawing sheet(s) including the correct The oath or declaration is objected to by the Examine	epted or b) objected to by the drawing(s) be held in abeyance. Se ion is required if the drawing(s) is ob	e 37 CFR 1.85(a). ejected to. See 37 CFR 1.	
Priority ι	under 35 U.S.C. § 119			
12)[a)	Acknowledgment is made of a claim for foreign All b) Some * c) None of: 1. Certified copies of the priority documents 2. Certified copies of the priority documents 3. Copies of the certified copies of the prior application from the International Bureau See the attached detailed Office action for a list	s have been received. s have been received in Applicati rity documents have been receive u (PCT Rule 17.2(a)).	ion No ed in this National Stag	je
2) 🔲 Notic 3) 🔯 Infor	tt(s) te of References Cited (PTO-892) te of Draftsperson's Patent Drawing Review (PTO-948) mation Disclosure Statement(s) (PTO-1449 or PTO/SB/08) tr No(s)/Mail Date 4/28/06.	4) Interview Summary Paper No(s)/Mail D 5) Notice of Informal F 6) Other:)

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DETAILED ACTION

1. Applicant's amendment necessitated the new ground(s) of rejection presented in this Office action. Accordingly, **THIS ACTION IS MADE FINAL**. See MPEP § 706.07(a). Applicant is reminded of the extension of time policy as set forth in 37 CFR 1.136(a).

A shortened statutory period for reply to this final action is set to expire THREE MONTHS from the mailing date of this action. In the event a first reply is filed within TWO MONTHS of the mailing date of this final action and the advisory action is not mailed until after the end of the THREE-MONTH shortened statutory period, then the shortened statutory period will expire on the date the advisory action is mailed, and any extension fee pursuant to 37 CFR 1.136(a) will be calculated from the mailing date of the advisory action. In no event, however, will the statutory period for reply expire later than SIX MONTHS from the date of this final action.

Claim Objections

2. Claims 12, 13, 25 and 26 are objected to under 37 CFR 1.75(c), as being of improper dependent form for failing to further limit the subject matter of a previous claim. Applicant is required to cancel the claim(s), or amend the claim(s) to place the claim(s) in proper dependent form, or rewrite the claim(s) in independent form.

Applicants amended present claims 1 and 14 such that the pendant solubility-promoting moiety (which can only be a fluoroalcohol, a carboxylic acid, an amino group, an imino group, a fluorinated imino group or a fluorinated amino group) is protected with the cyclic ketal acid labile moiety. In those claims 12, 13, 25 and 26, the solubility-

promoting group which is not protected with the cyclic ketal acid labile moiety has to be present whereas in present claims 1 and 14, the solubility-promoting moiety has to be protected with the cyclic ketal acid labile moiety. Thus, claims 12, 13, 25 and 26 fail to further limit the subject matter of claims 1 and 14. Besides, in those claims 12, 13, 25 and 26, the solubility-promoting group (both the free solubility-promoting group or the protected solubility-promoting group) is not limited only to those as recited in present claims 1 and 14.

Claim Rejections - 35 USC § 103

- 3. The text of those sections of Title 35, U.S. Code not included in this action can be found in a prior Office action.
- 4. Claims 1, 2, 5, 7-16, 19, 21-27 and 30 are rejected under 35 U.S.C. 103(a) as being unpatentable over Sooriyakumaran et al (US 2002/0081520 A1) in view of Asakawa et al (5,863,699) and Bucchignano et al (6,037,097).

In his Example 3, Sooriyakumaran teaches partial protection of poly(2-hydroxy-3,3,3-trifluoropropylsilsesquixoane) with acid-cleavable trimethylsilyl group.

Sooriyakumaran also teaches using a photoacid generator as the second component of his resist composition (see [0056]). Sooriyakumaran does not teach present cyclic ketal acid-labile moiety.

Asakawa et al teaches the equivalence of the trimethylsilyl group (which is taught in Sooriyakumaran) and 1-methoxycyclohexyl group as acid-decomposable groups (see col.12, line 36 and 41). Therefore, in view of Asakawa's teaching of equivalency, it would have been obvious to one skilled in the art to use 1-methoxycyclohexyl group in

partially protecting poly(2-hydroxy-3,3,3-trifluoropropylsilsesquioxane) in Sooriyakumaran's Example 3. Furthermore, Bucchignano teaches (col.2, lines 21-29, lines 35-53 and col.4, lines 37-50) that by using a cyclic aliphatic ketal substituent such as a methoxycyclohexanyl group as an acid labile protecting group for an aqueous base soluble copolymer, one can obtain a chemically amplified resist that provides improved resist coating shelf life and with little or no vacuum effects on use and that prevents airborned contaminants from adversely effecting the chemical nature of the aqueous base soluble copolymer. Bucchignano also teaches (col.4, lines 51-58) that hydrogen of the cycloaliphatic portions of the ketal substituent can be substituted with hydrophobic groups such as -CF₃, -CHF₂, -CH₂F, -CCl₃, -CHCl₂, -CH₂Cl, and -SI(CH₃)₃ in order to obtain additional etch resistance. In view of Asakawa, which shows that the trimethylsilyl group and methoxycyclohexyl group were art-recognized equivalent aciddecomposable groups, and further in view of Bucchignano's teaching that methoxycyclohexanyl group provides improved resist coating shelf life and little or no vacuum effects on use, it would have been obvious to one of ordinary skill in the art to use the methoxycyclohexanyl group (or methoxycyclohexanyl group substituted with CF₃, -CHF₂, -CH₂F, -CCl₃, -CHCl₂, -CH₂Cl, or -SI(CH₃)₃) as Sooriyakumaran's acidcleavable group in his Example 3 in order to obtain a chemically amplified resist that provides improved resist coating shelf life and with little or no vacuum effects on use and that prevents air-borned contaminants from adversely effecting the chemical nature of the aqueous base soluble copolymer. Therefore, Sooriyakumaran in view of Asakawa and Bucchignano would render obvious present inventions of claims 1, 2, 5,

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and 7-10 (i.e., those references teach present fluoroalcohol moiety (present pendant solubility promoting moiety) protected with present cyclic ketal acid-labile moiety):

because present specification (pg.13, lines 19-32) also lists

"methoxycyclohexanyl" group as one of preferred examples for cyclic ketal protecting groups that satisfy the first formula of claim 1, it follows that the methoxycyclohexanyl group, used as Sooriyakumaran's acid-cleavable group would inherently have a low activation energy less than about 20 kcal/mol for acid-catalyzed cleaving, and the same acid-cleavable group would inherently be cleavable at room temperature as presently recited.

Also, the poly(2-hydroxy-3,3,3-trifluoropropylsilsesquixoane) which is partially protected with methoxycyclohexanyl group as discussed above comprises present combination of monomeric units (II) and (III) in claims 12 and 25; *in the formula (III)*, X would be a methylene group, R³ would be a H atom, R⁴ would be –CF₃ (a fluorinated alkyl group), q would be 0, and R⁶ would be –OH (a solubility promoting group). In the formula (II), X would be a methylene group, R³ would be a H atom, R⁴ would be –CF₃ (a fluorinated alkyl group), q would be 0, and R⁶ would be methoxycyclohexanyl oxy group (present solubility inhibiting cyclic ketal group). Also, such polymer comprises present combination of monomeric units (II) and (V) in claims 13 and 26; in the formula (V), X would be a methylene group, one R³ would be a H atom, another R³ would be –CF₃ (a halogenated alkyl group), q would be 0, and R⁶ would be –OH (a solubility promoting group). Therefore, Sooriyakumaran in view of Asakawa and Bucchignano would render obvious present inventions of claims 12, 13, 25, and 26.

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With respect to present claim 11, Sooriyakumaran teaches ([0055]) that his copolymer generally has an average Mw in the range of 1,000 to 5,000. Therefore, Sooriyakumaran in view of Asakawa and Bucchignano would render obvious present invention of claim 11.

Sooriyakumaran teaches ([0075]) a process for generating a resist image on a substrate which comprises the steps of: (a) coating a substrate with a film comprising his resist composition; (b) imagewise exposing the film to radiation; and (c) developing the image. Sooriyakumaran teaches ([0080]) that the pattern from the resist structure may then be transferred to the material of the underlying substrate by etching.

Sooriyakumaran also teaches a post-exposure baking step (see [109]). Therefore, Sooriyakumaran in view of Asakawa and Bucchignano would render obvious present inventions of claims 14-16, 19, 21-24 and 30.

With respect to present claim 27, Sooriyakumaran teaches that a bilayer substrate may be employed in which his resist composition forms an upper resist layer on top of a bilayer substrate comprised of a base layer and underlayer that lies between the upper resist layer and the base layer. Thus, Sooriyakumaran in view of Asakawa and Bucchignano would render obvious present invention of claim 27.

5. Claims 28 and 29 are rejected under 35 U.S.C. 103(a) as being unpatentable over Sooriyakumaran et al (US 2002/0081520 A1) in view of Asakawa et al (5,863,699) and Bucchignano et al (6,037,097) as applied to claim 27 above, and further in view of Khojasteh et al (US 2002/0058204 A1).

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Sooriyakumaran in view of Asakawa and Bucchignano is discussed above in Paragraph 4. As discussed above, Sooriyakumaran teaches that a bilayer substrate may be employed in which his resist composition forms an upper resist layer on top of a bilayer substrate comprised of a base layer and underlayer that lies between the upper resist layer and the base layer. Sooriyakumaran does not teach present underlayer composition of claim 28. Khojasteh teaches ([0009]-[0021]) an underlayer composition comprising (a) a polymer containing (i) cyclic ether moieties, (ii) saturated polycyclic moieties, and (iii) aromatic moieties, and (b) an acid generator, or an underlayer composition comprising (a) a polymer containing (i) saturated polycyclic moieties, and (ii) aromatic moieties, (b) an acid generator, and (c) a crosslinker. Khojasteh teaches that use of such an underlayer composition provide underlayers having outstanding optical, mechanical and etch selectivity properties ([0008]). In view of Khojasteh's teaching, it would have been obvious to one of ordinary skill in the art to use Khojasteh's underlayer composition for Sooriyakumaran's underlayer in order to obtain underlayer having outstanding optical, mechanical and etch selectivity properties as taught by Khojasteh. Khojasteh also teaches ([0058]) that the polymer of the underlayer composition preferably contains a fluorine components such as pentafluoroaryl group and trifluoromethyl group. Therefore, Sooriyakumaran in view of Asakawa and Bucchignano and further in view of Khojasteh would render obvious present inventions of claims 28 and 29.

Response to Arguments

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6. Applicants argue that the solubility-promoting moiety such as fluoroalcohol as in present invention or as in Sooriyakumaran et al is even larger than the α-trifluoromethyl alcohol group of Schmaljohann et al, thus suggesting that an even more powerful catalyst may be required for the protection reaction, which could result in undesired side products. However, applicants have not provided any evidence on the record that for larger fluoroalcohol, more powerful catalyst is required for the protection reaction. Schmaljohann does not state such correlation as suggested by applicants. In fact, Schmaljohann states that the reason why the PVA is protected readily with THP whereas the α -trifluoromethyl alcohol groups is protected to only a small extent is because the α -trifluoromethylalcohol groups is acidic (thus, more powerful neutral catalysts like ATPB give high conversion for the protection reaction); Schmaljohann is not saying that reason why the PVA is protected readily with THP whereas the α trifluoromethyl alcohol groups is protected to only a small extent is because the α trifluoromethylalcohol group is larger than PVA. Also, with respect to applicants' statement (based on Sinta) that although the use of a stronger catalyst may results in a successful protection reaction, undesired side products may render the photoresist unsuitable for its intended purpose, what Sinta means by "stronger catalysts" is catalysts which are stronger in acidity. However, what is used in Schmaljohann is ATPB which is a neutral catalyst. Therefore, applicants' argument is found to be unpersuasive, and thus present rejection over Sooriyakumaran in view of Asakawa and Bucchignano still stands.

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pm EST.

7. Any inquiry concerning this communication or earlier communications from the examiner should be directed to Sin J. Lee whose telephone number is 571-272-1333. The examiner can normally be reached on Monday-Friday from 9:00 am EST to 5:30

If attempts to reach the examiner by telephone are unsuccessful, the examiner's

the organization where this application or proceeding is assigned is **571-273-8300**.

supervisor, Cynthia Kelly, can be reached on 571-272-1526. The fax phone number for

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&-J. L. S. Lee

July 8, 2006

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